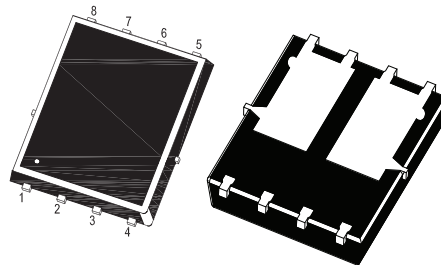
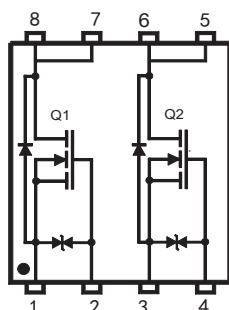


Dual N-Channel Enhancement Mode MOSFET

Features

- Low $R_{DS(ON)}$
- Halogen and Antimony Free(HAF), RoHS compliant
- Built-in G-S Protection Diode
- Typical ESD Protection HBM Class 2

Classification	Voltage Range(V)
0A	< 125
0B	125 to < 250
1A	250 to < 500
1B	500 to < 1000
1C	1000 to < 2000
2	2000 to < 4000
3A	4000 to < 8000
3B	≥ 8000



Q1:1.Source 2.Gate 7.Drain 8.Drain
 Q2:3.Source 4.Gate 5.Drain 6.Drain
 DFN5060 Plastic Package

Key Parameters (Q1/Q2)

Parameter	Value	Unit
BV_{DSS}	40	V
$R_{DS(ON)} \text{ Max}$	9.9 @ $V_{GS} = 10 \text{ V}$	m Ω
	12.6 @ $V_{GS} = 4.5 \text{ V}$	
$V_{GS(th)} \text{ typ}$	1.5	V
$Q_g \text{ typ}$	48 @ $V_{GS} = 10 \text{ V}$	nC

Application

- Load Switch
- DC-DC converters and Off-line UPS

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified) (Q1/Q2)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	36	A
		22	
Peak Drain Current, Pulsed ¹⁾	I_{DM}	200	A
Avalanche Current	I_{AS}	26.8	A
Single Pulse Avalanche Energy ²⁾	E_{AS}	36	mJ
Total Power Dissipation	P_{tot}	28.8	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	$^\circ\text{C}$

Thermal Characteristics (Q1/Q2)

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	5.2	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient ³⁾	$R_{\theta JA}$	60	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 175^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.1 \text{ mH}$, $R_g = 25 \Omega$, $I_{AS} = 26.8 \text{ A}$, $V_{GS} = 10 \text{ V}$.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at T_a = 25°C unless otherwise specified (Q1/Q2)

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at I _D = 250 μA	BV _{DSS}	40	-	-	V
Drain-Source Leakage Current at V _{DS} = 32 V	I _{DSS}	-	-	1	μA
Gate Leakage Current at V _{GS} = ± 16 V	I _{GSS}	-	-	± 10	μA
Gate-Source Threshold Voltage at V _{DS} = V _{GS} , I _D = 250 μA	V _{GS(th)}	1	-	2.5	V
Drain-Source On-State Resistance at V _{GS} = 10 V, I _D = 12 A at V _{GS} = 4.5 V, I _D = 10 A	R _{DS(on)}	- -	8.8 -	9.9 12.6	mΩ
DYNAMIC PARAMETERS					
Forward Transconductance at V _{DS} = 5 V, I _D = 12 A	g _{fs}	-	24	-	S
Gate resistance at V _{DS} = 0 V, V _{GS} = 0 V, f = 1 MHz	R _g	-	0.8	-	Ω
Input Capacitance at V _{GS} = 0 V, V _{DS} = 20 V, f = 1 MHz	C _{iss}	-	2268	-	pF
Output Capacitance at V _{GS} = 0 V, V _{DS} = 20 V, f = 1 MHz	C _{oss}	-	168	-	pF
Reverse Transfer Capacitance at V _{GS} = 0 V, V _{DS} = 20 V, f = 1 MHz	C _{rss}	-	121	-	pF
Gate charge total at V _{GS} = 10 V, V _{DS} = 20 V, I _D = 12 A at V _{GS} = 4.5 V, V _{DS} = 20 V, I _D = 12 A	Q _g	- -	48 23	- -	nC
Gate to Source Charge at V _{GS} = 10 V, V _{DS} = 20 V, I _D = 12 A	Q _{gs}	-	8	-	nC
Gate to Drain Charge at V _{GS} = 10 V, V _{DS} = 20 V, I _D = 12 A	Q _{gd}	-	9	-	nC
Turn-On Delay Time at V _{GS} = 10 V, V _{DS} = 20 V, I _D = 12 A, R _g = 3.3 Ω	t _{d(on)}	-	17	-	ns
Turn-On Rise Time at V _{GS} = 10 V, V _{DS} = 20 V, I _D = 12 A, R _g = 3.3 Ω	t _r	-	30	-	ns
Turn-Off Delay Time at V _{GS} = 10 V, V _{DS} = 20 V, I _D = 12 A, R _g = 3.3 Ω	t _{d(off)}	-	17	-	ns
Turn-Off Fall Time at V _{GS} = 10 V, V _{DS} = 20 V, I _D = 12 A, R _g = 3.3 Ω	t _f	-	2	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at I _S = 1 A, V _{GS} = 0 V	V _{SD}	-	-	1.2	V
Body-Diode Continuous Current	I _S	-	-	36	A
Body-Diode Continuous Current, Pulsed	I _{SM}	-	-	200	A
Body Diode Reverse Recovery Time at I _S = 12 A, di/dt = 100 A / μs	t _{rr}	-	13	-	ns
Body Diode Reverse Recovery Charge at I _S = 12 A, di/dt = 100 A / μs	Q _{rr}	-	6	-	nC

Electrical Characteristics Curves (Q1/Q2)

Fig. 1 Typical Output Characteristics

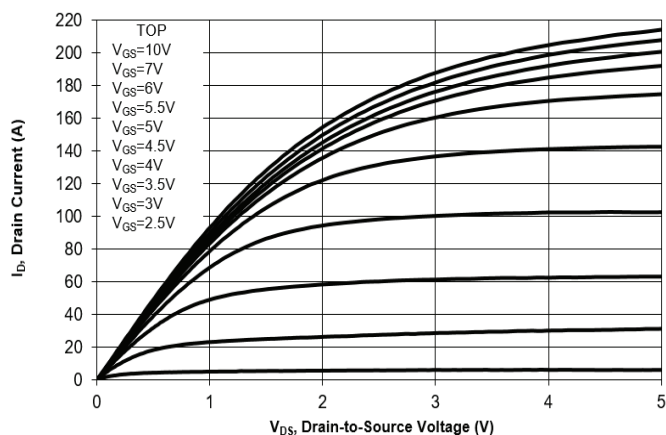


Fig. 2 Typical Transfer Characteristics

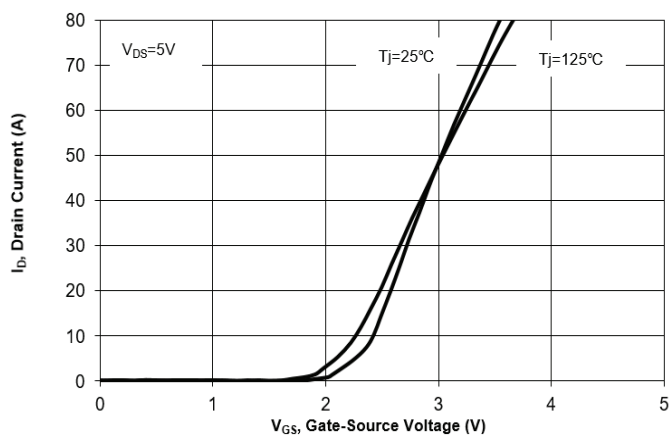


Fig. 3 On-Resistance vs. Drain Current

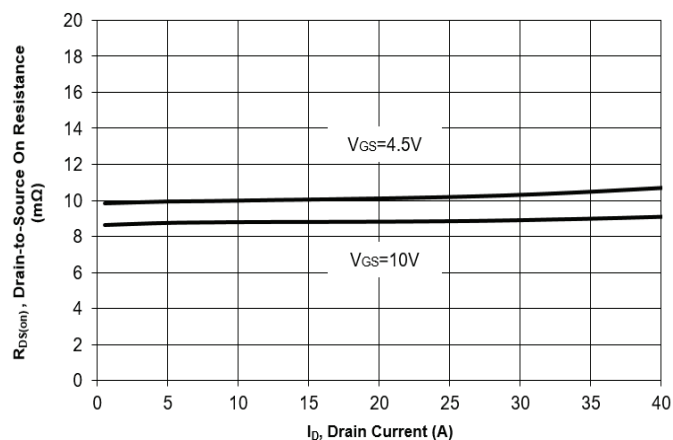


Fig. 4 On-Resistance vs. Gate to Source Voltage

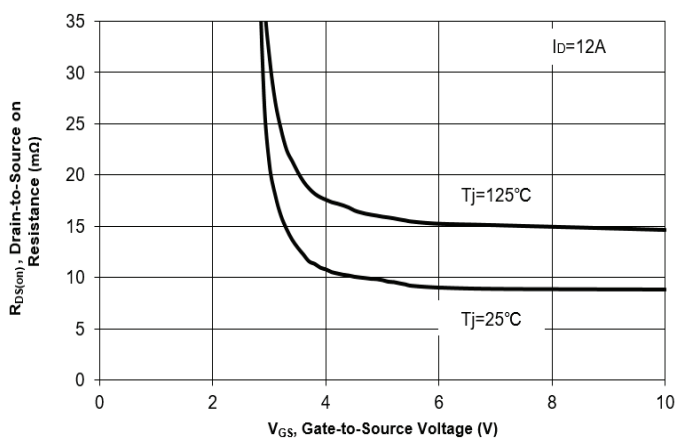


Fig. 5 On-Resistance vs. T_J

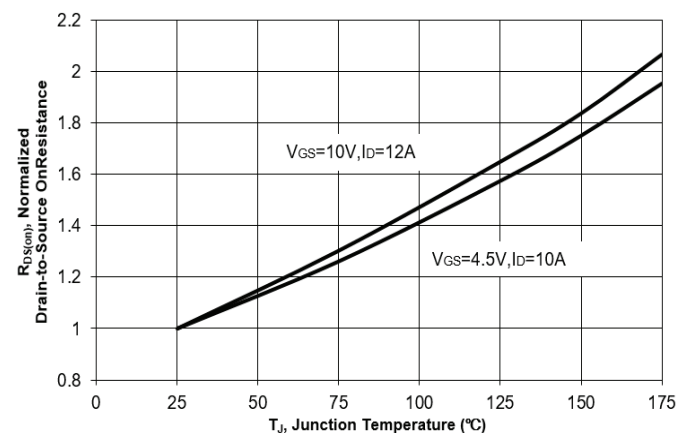
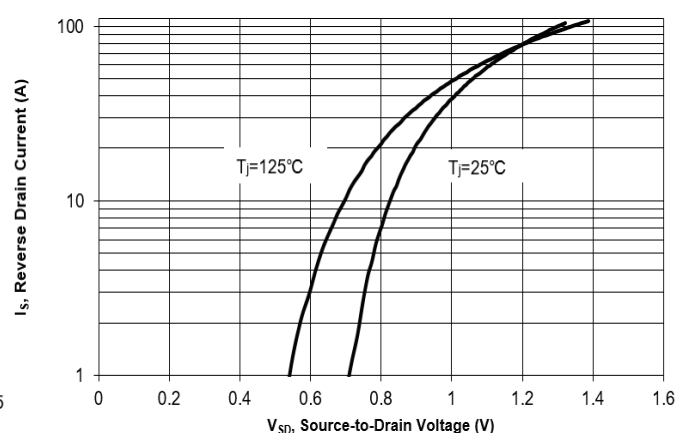


Fig. 6 Typical Body Diode Forward Characteristics



Electrical Characteristics Curves (Q1/Q2)

Fig. 7 Typical Junction Capacitance

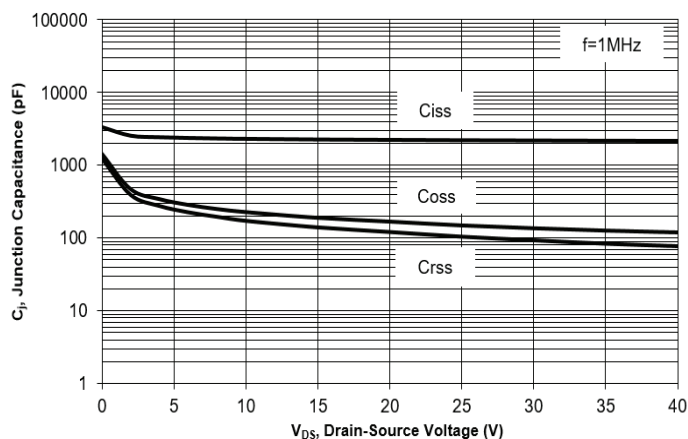


Fig. 8 Drain-Source Leakage Current vs. T_J

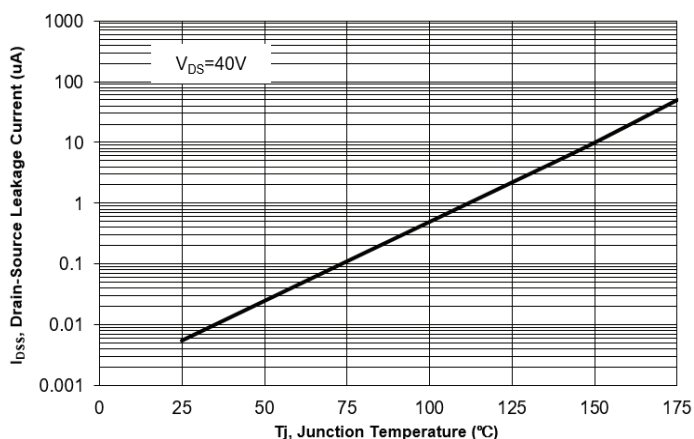


Fig. 9 V_{(BR)DSS} vs. Junction Temperature

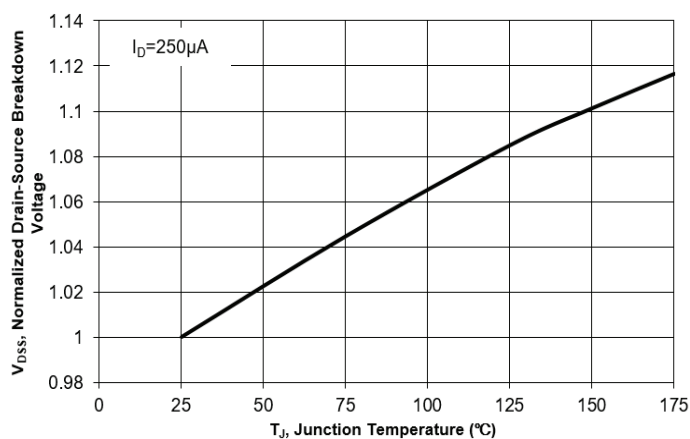


Fig. 10 Gate Threshold Variation vs. T_J

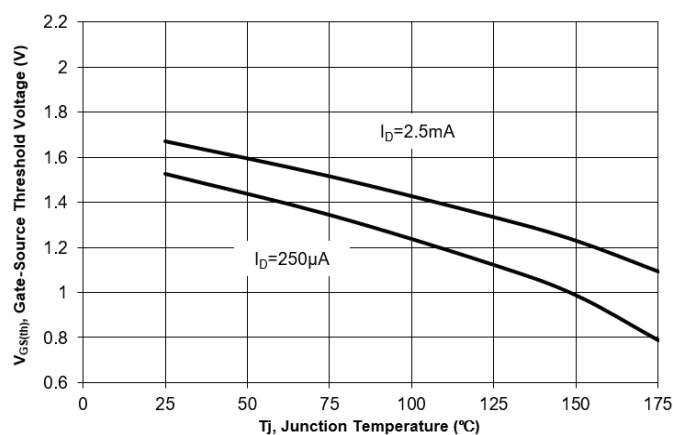


Fig. 11 Gate Charge

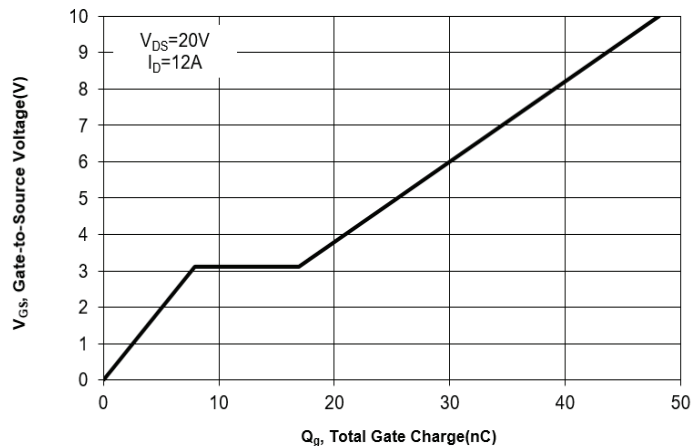
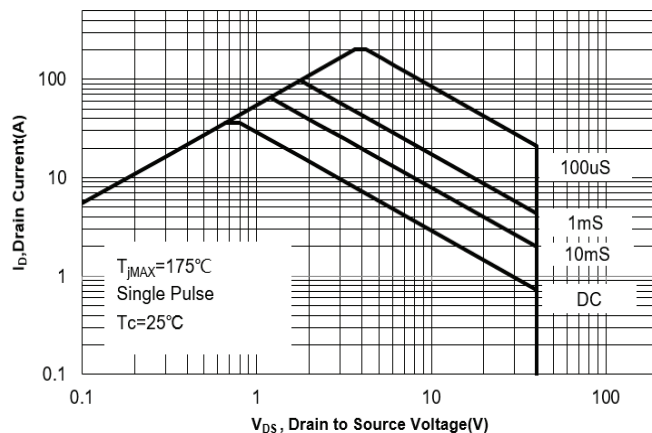


Fig. 12 Safe Operation Area



Electrical Characteristics Curves (Q1/Q2)

Fig.13 Normalized Maximum Transient Thermal Impedance($Z_{\theta JC}$)

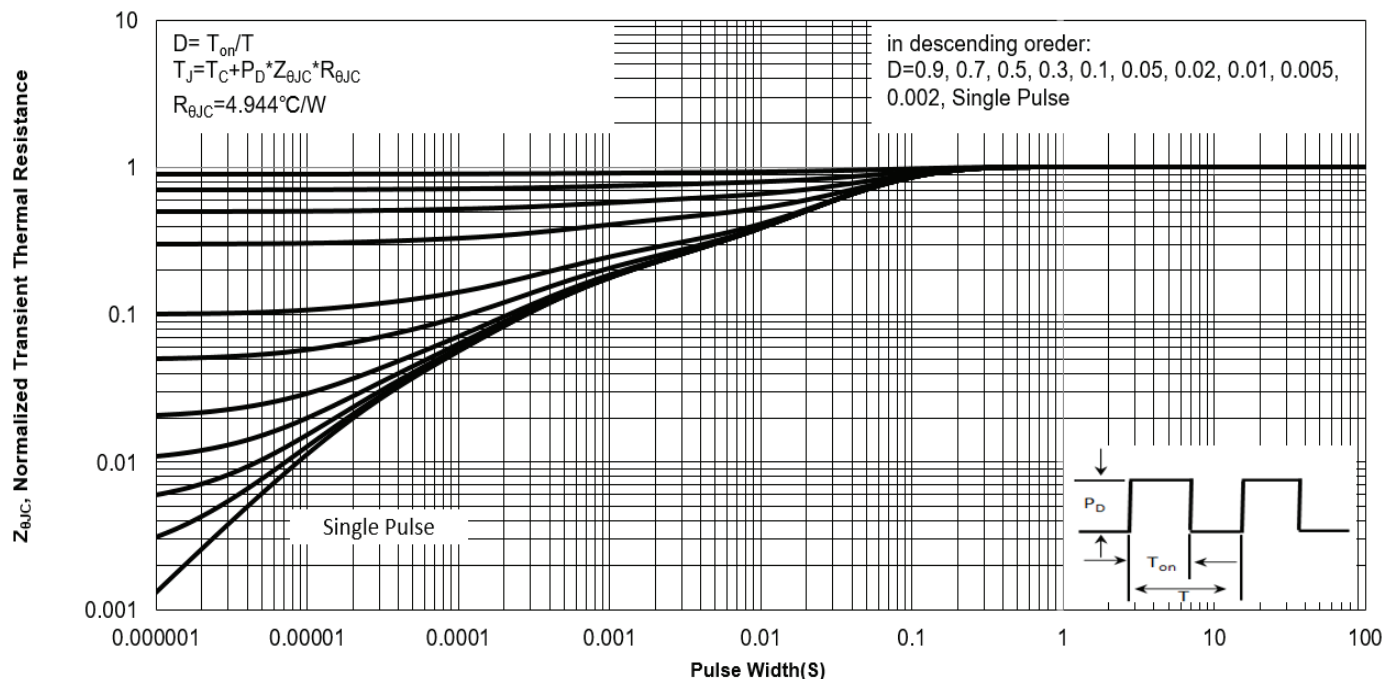
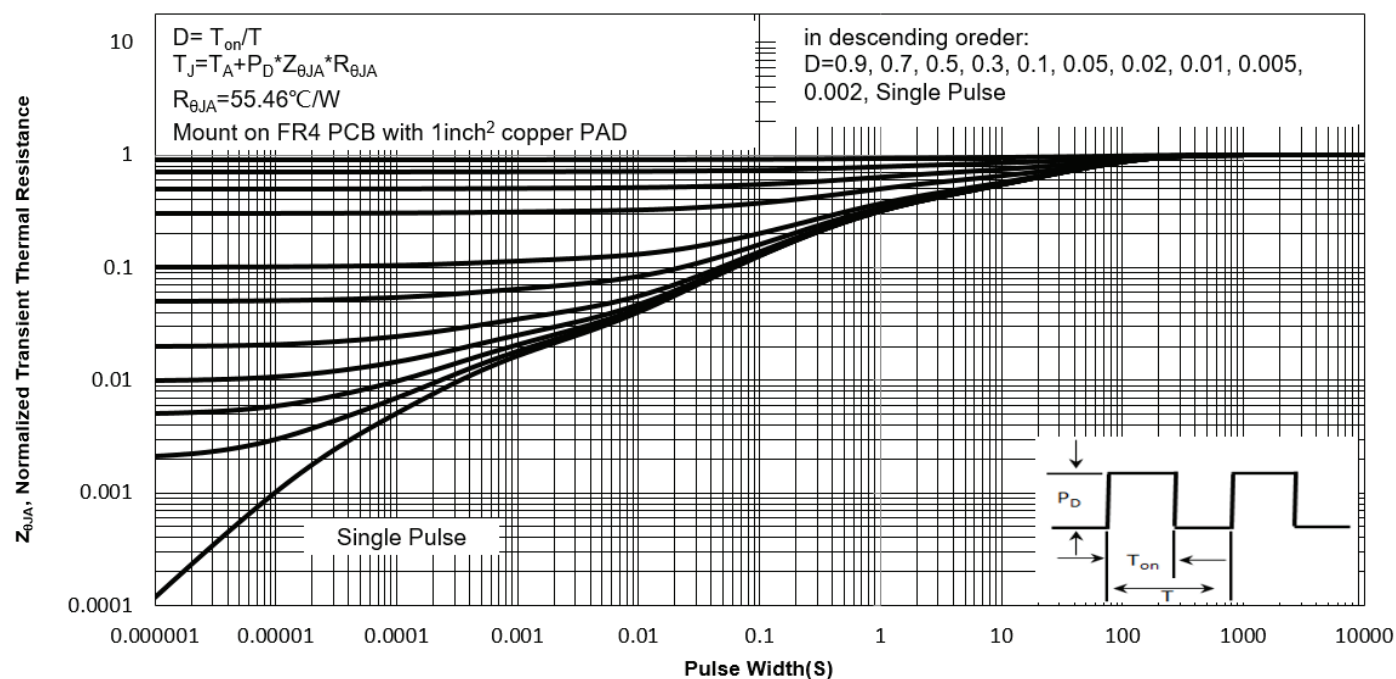


Fig.14 Normalized Maximum Transient Thermal Impedance($Z_{\theta JA}$)



Test Circuits (Q1/Q2)

Fig.1-1 Switching times test circuit

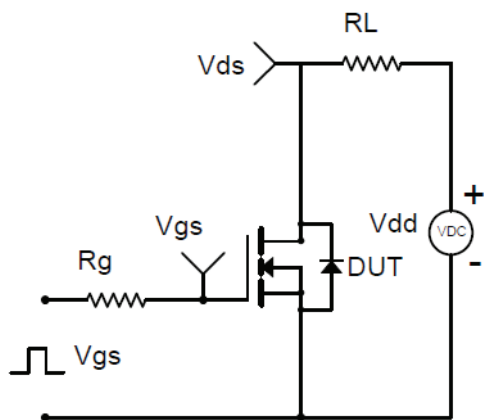


Fig.1-2 Switching Waveform

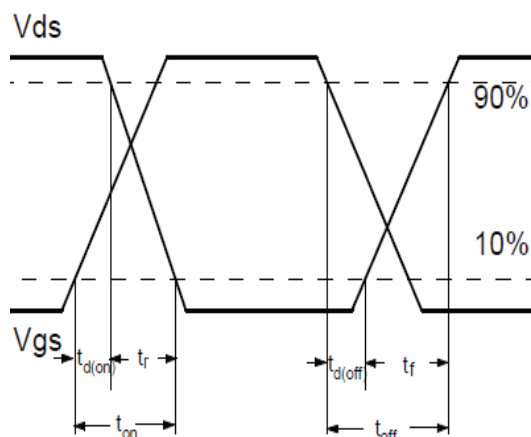


Fig.2-1 Gate charge test circuit

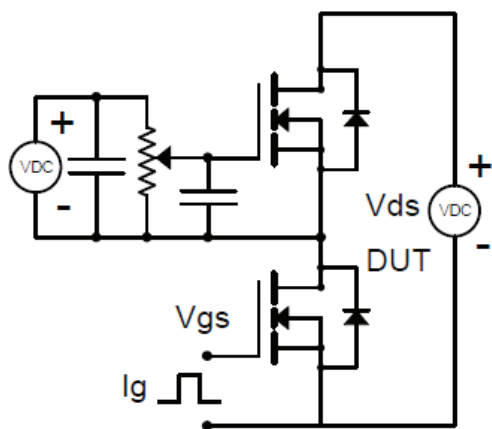


Fig.2-2 Gate charge waveform

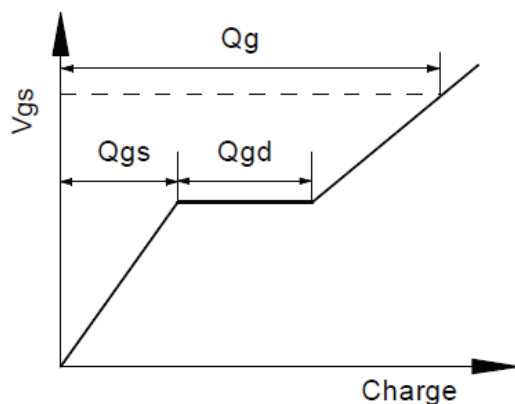


Fig.3-1 Avalanche test circuit

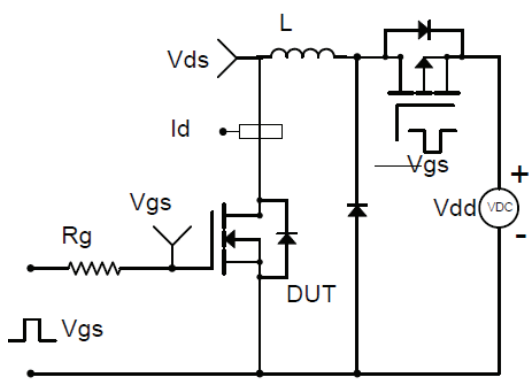
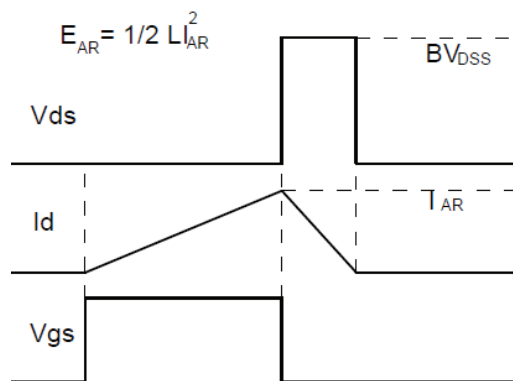
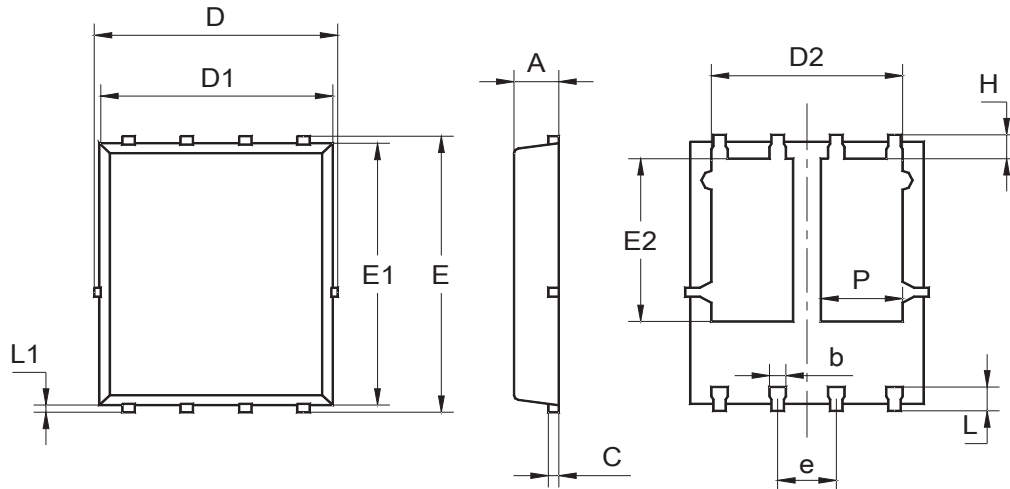


Fig.3-2 Avalanche waveform



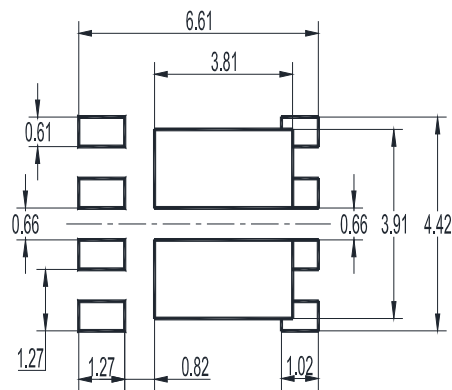
Package Outline Dimensions (Units: mm)

DFN5060



Unit	A	b	C	D	D1	D2	E	E1	E2	e	L	L1	H	P
mm	1.12 0.9	0.51 0.33	0.34 0.11	5.26 4.7	5.1 4.7	4.5 3.56	6.25 5.75	6 5.6	3.66 3.18	1.37 1.17	0.71 0.35	0.2 0.06	0.71 0.35	2.0 1.6

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN5060	12	8 ± 0.1	0.315 ± 0.004	330	13	5,000

Marking information

" TM604D099LSZK " = Part No.

" ***** " = Date Code Marking

Font type: Arial

